

**Amendments to the Claims:**

1. (Previously Presented) A method for etching a ruthenium film, comprising:  
etching a ruthenium film formed on a substrate with a chemical liquid having a pH of not less than 12 and an oxidation-reduction potential of not less than 300 mVvsSHE.
2. (Previously Presented) The method according to claim 1, wherein said chemical liquid is maintained at a pH of not less than 12 by using ammonia, an organic alkali or an alkali hydroxide.
3. (Previously Presented) The method according to claim 1, wherein said chemical liquid is maintained at an oxidation-reduction potential of not less than 300 mVvsSHE by using a halide oxidant.
4. (Currently Amended) The method according to claim 1, wherein said chemical liquid comprises ~~a strongly~~ an alkaline oxidant solution or a mixed solution of an alkali solution and an oxidant solution, and said ~~strongly~~ alkaline oxidant solution or said mixed solution is supplied to a predetermined portion of the ruthenium film formed on the substrate.
5. (Currently Amended) The method according to claim 4, wherein said ~~strongly~~ alkaline oxidant solution comprises a solution of a halogenated oxygen acid salt selected from hypochlorite, chlorite, and bromate.
6. (Previously Presented) The method according to claim 4, wherein said alkali solution contains at least one of ammonia, tetramethylammonium hydroxide, and trimethylamine;  
wherein said oxidant solution contains at least one of bromine, iodine, chlorine dioxide, and ozone.

7. (Currently Amended) The method according to claim 1, further comprising;  
supplying an alkali solution and an oxidant solution separately to a predetermined portion of the ruthenium film formed on the substrate; and  
mixing said ~~both solutions~~ alkali solution and said oxidant solution at said predetermined portion to prepare said chemical liquid.

8. (Previously Presented) The method according to claim 7, wherein said alkali solution contains at least one of ammonia, tetramethylammonium hydroxide, and trimethylamine;  
wherein said oxidant solution contains at least one of bromine, iodine, chlorine dioxide, and ozone.

Claims 9-17 (Cancelled).

18. (New) The method according to claim 1, wherein said etching comprises:  
rotating said substrate while simultaneously supplying water to a central portion of a first side of said substrate, simultaneously supplying said chemical liquid to a peripheral region of said first side of said substrate, and simultaneously supplying said chemical liquid to a central portion of a second side of said substrate opposite said first side, said ruthenium film being formed at said first side of said substrate.

19. (New) The method according to claim 1, wherein said etching comprises:  
rotating said substrate while simultaneously supplying water to a central portion of a first side of said substrate, and simultaneously supplying said chemical liquid to a peripheral region of said substrate via a rotatable sponge roll, said ruthenium film being formed at said first side of said substrate.

20. (New) The method according to claim 1, wherein said etching comprises:

rotating said substrate by producing a flow of inert gas from a lower surface of a Bernoulli chuck toward a first side of said substrate, said ruthenium film being formed at said first side of said substrate; and

simultaneously supplying said chemical liquid to a second side of said substrate opposite said first side.